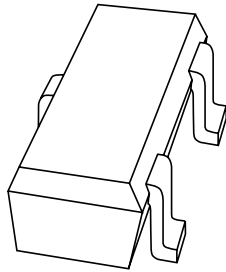


DATA SHEET



2PB710A PNP general purpose transistor

Product data sheet
Supersedes data of 1999 Apr 23

1999 May 31



PNP general purpose transistor

2PB710A

FEATURES

- High current (max. 500 mA)
- Low voltage (max. 50 V).

APPLICATIONS

- General purpose switching and amplification.

DESCRIPTION

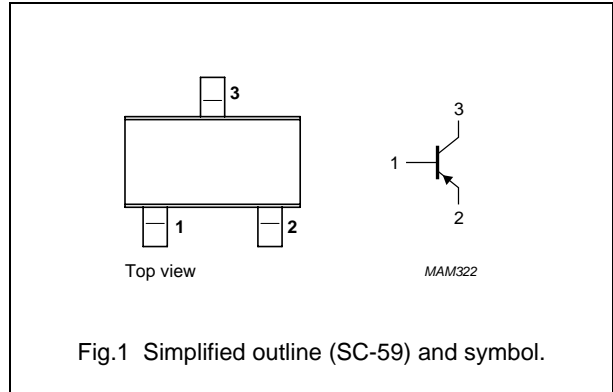
PNP transistor in an SC-59 plastic package.
NPN complement: 2PD602A.

MARKING

TYPE NUMBER	MARKING CODE
2PB710AQ	DQ
2PB710AR	DR
2PB710AS	DS

PINNING

PIN	DESCRIPTION
1	base
2	emitter
3	collector



LIMITING VALUES

In accordance with the Absolute Maximum Rating System (IEC 134).

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
V_{CBO}	collector-base voltage	open emitter	-	-60	V
V_{CEO}	collector-emitter voltage	open base	-	-50	V
V_{EBO}	emitter-base voltage	open collector	-	-5	V
I_C	collector current (DC)		-	-500	mA
I_{CM}	peak collector current		-	-1	A
I_{BM}	peak base current		-	-200	mA
P_{tot}	total power dissipation	$T_{amb} \leq 25\text{ }^\circ\text{C}$; note 1	-	250	mW
T_{stg}	storage temperature		-65	+150	$^\circ\text{C}$
T_j	junction temperature		-	150	$^\circ\text{C}$
T_{amb}	operating ambient temperature		-65	+150	$^\circ\text{C}$

Note

1. Transistor mounted on an FR4 printed-circuit board.

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THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
$R_{th\ j-a}$	thermal resistance from junction to ambient	note 1	500	K/W

Note

1. Transistor mounted on an FR4 printed-circuit board.

CHARACTERISTICS

$T_{amb} = 25\text{ °C}$ unless otherwise specified.

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT				
I_{CBO}	collector cut-off current	$I_E = 0; V_{CB} = -60\text{ V}$	–	–10	nA				
		$I_E = 0; V_{CB} = -60\text{ V}; T_j = 150\text{ °C}$	–	–5	μA				
I_{EBO}	emitter cut-off current	$I_C = 0; V_{EB} = -5\text{ V}$	–	–10	nA				
h_{FE}	DC current gain	$I_C = -150\text{ mA}; V_{CE} = -10\text{ V};$ note 1	85	170					
						2PB710AQ			
						2PB710AR			
	2PB710AS	120	240						
DC current gain	$I_C = -500\text{ mA}; V_{CE} = -10\text{ V};$ note 1	40	–						
V_{CEsat}	collector-emitter saturation voltage	$I_C = -300\text{ mA}; I_B = -30\text{ mA};$ note 1	–	–600	mV				
V_{BEsat}	base-emitter saturation voltage	$I_C = -300\text{ mA}; I_B = -30\text{ mA};$ note 1	–	–1.5	V				
C_c	collector capacitance	$I_E = I_e = 0; V_{CB} = -10\text{ V}; f = 1\text{ MHz}$	–	15	pF				
f_T	transition frequency	$I_C = -50\text{ mA}; V_{CE} = -10\text{ V};$ $f = 100\text{ MHz};$ note 1	100	–	MHz				
						2PB710AQ			
						2PB710AR	120	–	MHz
						2PB710AS	140	–	MHz

Note

1. Pulse test: $t_p \leq 300\text{ }\mu\text{s}; \delta \leq 0.02.$

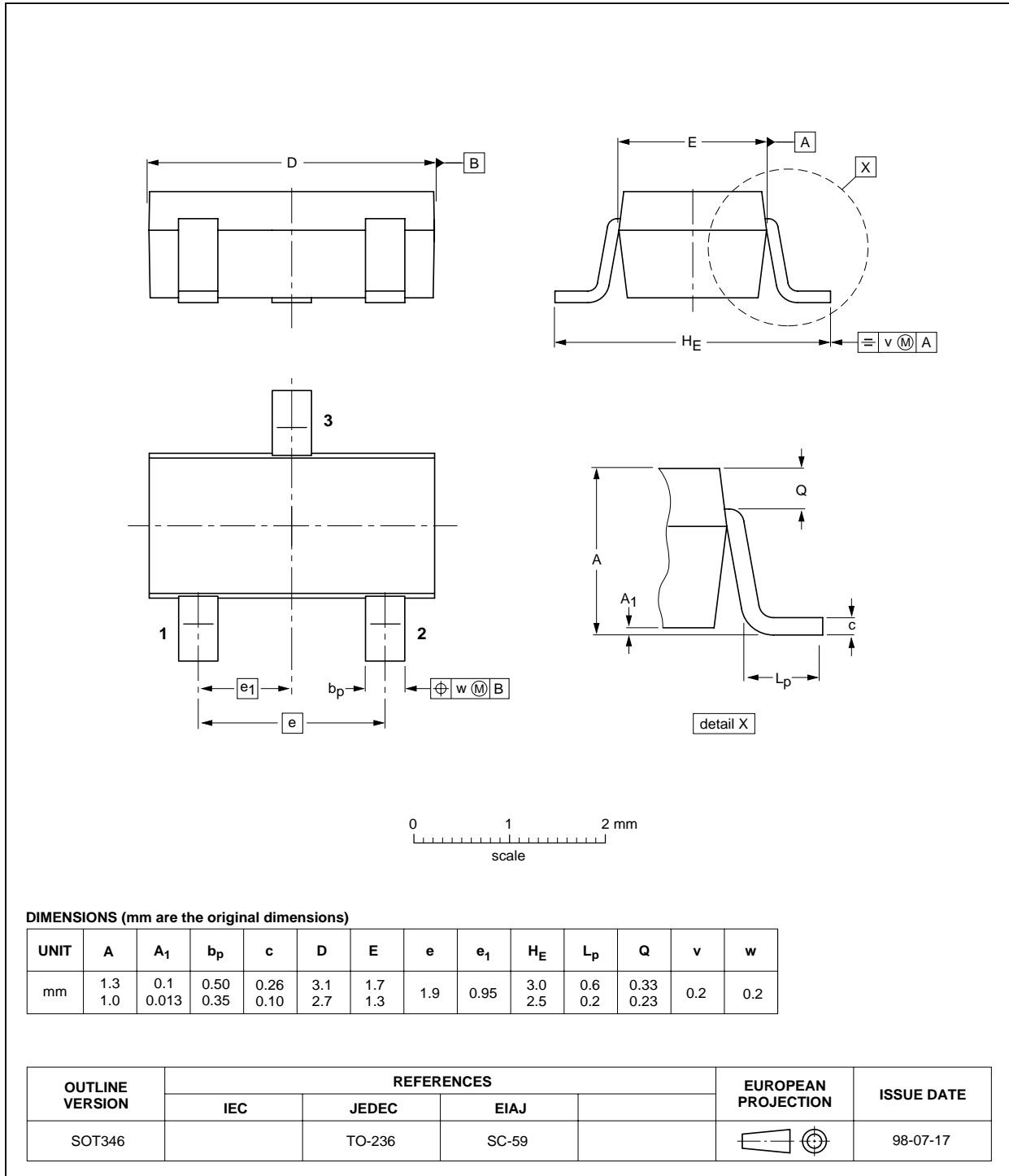
PNP general purpose transistor

2PB710A

PACKAGE OUTLINE

Plastic surface mounted package; 3 leads

SOT346



PNP general purpose transistor

2PB710A

DATA SHEET STATUS

DOCUMENT STATUS ⁽¹⁾	PRODUCT STATUS ⁽²⁾	DEFINITION
Objective data sheet	Development	This document contains data from the objective specification for product development.
Preliminary data sheet	Qualification	This document contains data from the preliminary specification.
Product data sheet	Production	This document contains the product specification.

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Contact information

For additional information please visit: <http://www.nxp.com>

For sales offices addresses send e-mail to: salesaddresses@nxp.com

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Printed in The Netherlands

115002/06/pp6

Date of release: 1999 May 31

Document order number: 9397 750 05863

